Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A method of forming a multilayer dielectric film on a substrate, comprising the steps of:

forming a metal silicate layer on the surface of the substrate, wherein said metal silicate layer includes more than one metal element;

forming a metal oxide layer atop the metal silicate layer, wherein said metal oxide layer includes more than one metal element; and

forming another metal silicate layer atop the metal oxide layer, wherein said metal silicate layers each have a thickness and a dielectric constant lower than the metal oxide layer.

2. (cancelled)

3. (previously presented) The method of claim 1 wherein said forming steps are carried out by any one of, or combination of, chemical vapor deposition (CVD), physical vapor deposition (PVD), atomic layer deposition (ALD), aerosol pyrolysis, spray coating or spin-on-coating.

4. (previously presented) The method of claim 1 wherein said forming steps are carried out by chemical vapor deposition (CVD) and using an oxygen source selected from the group consisting of O_2, O_3, NO, N_2O, H_2O, OH^-, alcohol, alkoxides, and H_2O_2.

5. (cancelled)

6. (previously presented) The method of claim 1 wherein said metal oxide layer comprises a layer of a metal oxide having a dielectric constant in a range of 15 to 200 and

wherein each of said metal silicate layers comprises a layer of a metal silicate having a dielectric constant in a range of 5 to 100.

7-9. (cancelled)

10. (previously presented) The method of claim 6 wherein said metal silicate has the formula of M_xSiO_y, where M is a metal selected from the group consisting of Zr, Hf, Ti, V, Nb, Ta, Cr, Mo, W, Mn, Zn, Al, Ga, In, Ge, Sr, Pb, Sb, Bi, Sc, Y, La, Be, Mg, Ca, Sr, Ba, Th, Lanthanides (Ce, Pr, Nd, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb, Lu), and mixtures thereof, x is a number in the range of 1 to 3, and y is a number in the range of 2 to 5.

11. (cancelled)

12. (previously presented) The method of claim 10 wherein said metal silicate is selected from the group consisting of Zr_x-Si-O_y and Hf_x-Si-O_y, x is a number in the range of 1 to 3, and y is a number in the range of 2 to 5.

13. (cancelled)

14. (previously presented) The method of claim 1 wherein said metal oxide layer has a thickness in a range of about 30 to 80Å.

15. (previously presented) The method of claim 1 wherein said metal silicate layers has a thickness of one to two atomic layers.